

Numerical analysis of suppression effects on optical feedback noise by superposition of high frequency current in semiconductor lasers

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Numerical Analysis of Suppression Effects on Optical Feedback Noise by Superposition of High Frequency Current in Semiconductor Lasers

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Abstract— Semiconductor lasers tend to be suffered by the optical feedback (OFB) noise caused by reflection of the output light at surface of the optical disc or the optical fiber. Superposition of high frequency (HF) current is used as a technique to suppress the OFB noise. However, this is not effective when frequency of the HF current coincides with a rational number of the round trip time for the OFB. This paper shows numerical simulations on the phenomena of the OFB noise, its suppression by the superposition of HF current and conditions at which the HF current was unable to suppress the noise. The model used here was based on multimode rate equations that include non-linear gain, Langevin noise sources, the OFB and the HF superposition. Generating mechanism of the OFB noise and its suppression are explained with approximated but analytical equations. Excellent correspondence between experimental data and simulation is also demonstrated.

Index Terms— Optical feedback noise, semiconductor laser, mode hopping, high frequency current, intensity noise, modulation.

I. INTRODUCTION

SEMICONDUCTOR lasers play a central role in the growing world of optoelectronic technologies. A measure of the importance of this emerging optoelectronic technology is provided by the optical disc players and the optical fiber communication system. It has been recognized that optical feedback (OFB), which is induced by the re-injection of output light into the laser followed by reflection at the surface of connecting optical device, causes excess noise in the output of the laser [1]. This excess noise is called OFB noise. Experiments show that the noise level is increased by 20dB or more as a result of the optical feedback [2]. The increase of noise degrades performance of the system.

Intense research activity has been focused on the suppression of the OFB noise of the lasers [3]-[10]. Superposition of high-frequency (HF) current is the most

popularly used method to suppress OFB noise. The OFB noise is well suppressed by suitable selections of frequency and amplitude of the superposed current. However, it has been experimentally reported that the OFB noise is not suppressed when frequency of the superposed current and round-trip frequency of the OFB are in relation of rational numbers [10]. Author's group of this paper gave a theoretical analysis on this problem based on mode competition phenomena among external cavity modes which are built in the space between laser front facet and the reflecting point of OFB [10]. Since author's previous analysis was based on small signal approximation, quantitative assessment for conditions unable to suppress OFB noise was difficult.

In this paper, we present a new model by which generation of the OFB noise and its suppression by the superposition of HF current can be numerically simulated. Conditions unable to suppress the OFB noise are evidently shown.

Our model was applied to 850nm GaAs lasers, and characteristics of the OFB noise are expressed in terms of relative intensity noise (RIN).

In the next section, model of analysis and basic equations are derived. In Sec. III, procedure of numerical calculation is explained. In Sec. IV, characteristics of the OFB noise without superposition of the HF current are examined to understand the mechanism of noise generation. In Sec. V, ability of noise suppression by help of superposition of the HF current is demonstrated. In Sec. VI, mechanism of the noise suppression is explained based on approximated equations. In Sec. VII, situations unable to suppress the noise are examined based on calculated data. In Sec. VIII, conclusions are given.

II. MODEL OF ANALYSIS

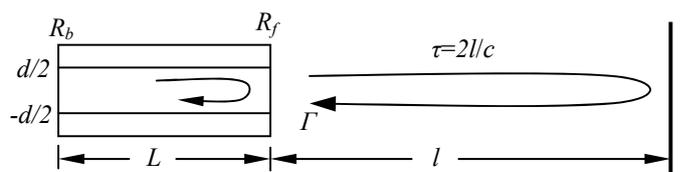


Fig. 1: Operation of a semiconductor laser under optical feedback.

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Operation of a semiconductor laser under OFB is illustrated in Fig. 1, where output light from the laser is reflected back from an external mirror and re-injected into the laser. The cavity length and the effective refractive index of the laser are L and n_r , respectively. The distance between the laser and the external mirror is l . Power reflectivity of the front facet is R_f . Ratio of the OFB to the front facet is Γ . The round-trip time is $\tau=2l/c$, where c is the speed of light in vacuum.

The electric component of the lasing field is described as follows.

$$E(\mathbf{r}, t) = \sum_p \tilde{E}_p(t) \Phi_p(\mathbf{r}) \exp(j\omega_p t) + c.c. \quad (1)$$

where $p=0, \pm 1, \pm 2, \pm 3, \dots$ is an index to indicate each longitudinal mode of the solitary laser, $\tilde{E}_p(t)$ is a slowly time-varying complex amplitude which is defined with an optical phase $\theta_p(t)$ as

$$\tilde{E}_p(t) = |\tilde{E}_p(t)| \exp(j\theta_p) \quad (2)$$

$\Phi_p(\mathbf{r})$ is a field spatial distribution function normalized as

$$\int_0^L \int_{-\infty}^{\infty} \int_{-\infty}^{\infty} |\Phi_p(\mathbf{r})|^2 dx dy dz = 1 \quad (3)$$

We suppose here that the transverse mode is stable fundamental mode.

Electric field amplitude $|\tilde{E}_p(t)|$ can be transformed to photon number $S_p(t)$ using the following relationship postulated by quantization of the lasing field [12]

$$2\varepsilon |\tilde{E}_p|^2 = \begin{cases} (S_p + 1)\hbar\omega & \text{for optical emission} \\ S_p\hbar\omega & \text{for optical absorption} \end{cases} \quad (4)$$

where ε is the dielectric constant of the active region.

Based on above mentioned notations, the rate equations for the modal photon number $S_p(t)$, modal phase $\theta_p(t)$ and number of injected electrons $N(t)$ can be obtained as [13-16]

$$\frac{dS_p}{dt} = \left(G_p - G_{tho} + \frac{c}{n_r L} \ln|U_p| \right) S_p + \frac{a\xi N/V}{\left[2 \frac{(\lambda_p - \lambda_0)^2}{\delta\lambda} \right]^2 + 1} + F_{Sp}(t) \quad (5)$$

$$\frac{d\theta_p}{dt} = \frac{1}{2} \left[\frac{\alpha a \xi}{V} (N - \bar{N}) - \frac{c}{n_r L} \varphi \right] + F_{\theta_p}(t) \quad (6)$$

$$\frac{dN}{dt} = -\sum_p A_p S_p - \frac{N}{\tau_s} + \frac{I}{e} \quad (7)$$

where G_p is the gain of the mode p whose wavelength is λ_p . G_{tho} is the threshold gain of the solitary laser. U_p is a function counting contribution of the OFB to the instantaneous photon number $S_p(t)$ of the mode p . These parameters are defined as

$$G_p = A_p - B_p S_p - \sum_{q \neq p} (D_{p(q)} + H_{p(q)}) S_q \quad (8)$$

$$G_{tho} = \frac{c}{n_r} \left[k + \frac{1}{2L} \ln \frac{1}{R_f R_b} \right] \quad (9)$$

$$U_p = 1 + (1 - R_f) \sqrt{\frac{\eta \Gamma}{R_f}} \exp(-j\omega_p \tau) \sqrt{\frac{S_p(t - \tau)}{S_p(t)}} \exp(j\{\theta_p(t - \tau) - \theta_p(t)\}) \\ = |U_p| \exp(-j\varphi) \quad (10)$$

$$\varphi = -\tan^{-1} \frac{\text{Im} U_p}{\text{Re} U_p} + m\pi \quad (-\pi \leq \varphi \leq \pi) \quad (11)$$

Here, A_p is the linear gain, B_p is the coefficient of self-suppression, and $D_{p(q)}$ and $H_{p(q)}$ are the coefficients of symmetric gain saturation and asymmetric gain saturation, respectively. These coefficients are given by [14]

$$A_p = \frac{a\xi}{V} [N - N_g - bV(\lambda_p - \lambda_0)^2] \quad (12)$$

$$B_p = \frac{9}{4} \frac{\hbar\omega}{\varepsilon_0 n_r^2} \left(\frac{\xi \tau_{in}}{\hbar V} \right)^2 a R_{cv}^2 (N - N_s) \quad (13)$$

$$D_{p(q)} = \frac{4}{3} \frac{B_p}{\left(\frac{2\pi c \tau_{in}}{\lambda_p^2} \right)^2 (\lambda_p - \lambda_q)^2 + 1} \quad (14)$$

$$H_{p(q)} = \frac{3\lambda_p^2}{8\pi c} \left(\frac{a\xi}{V} \right)^2 \frac{\alpha(N - N_g)}{\lambda_q - \lambda_p} \quad (15)$$

In (5), a is the differential gain coefficient, ξ is the field confinement factor, V is the volume of the active region, λ_0 is the peak wavelength and $\delta\lambda$ is the half-width of spontaneous emission. In (6) α is the linewidth enhancement factor and \bar{N} is the time average value of $N(t)$. In (7), τ_s is the electron lifetime, I is the injection current and e is the electron charge. In (9), k is the internal loss in the laser cavity. In (10), η is the coupling coefficient into the active region, Γ is the optical feedback ratio to the laser cavity, $\omega_p=2\pi c/\lambda_p$ is the angular frequency of mode p , $\omega_p \tau$ is the phase delay of the field in the roundtrip time. In (12)-(15), N_g is the electron number at transparency, b is the width of the linear gain coefficient, \hbar is the reduced Planck constant, $\omega=2\pi c/\lambda_0$ is the central angular frequency, τ_{in} is the intraband relaxation time, R_{cv} is the dipole moment and N_s is the electron number characterizing the self-suppression coefficient.

$F_{Sp}(t)$ and $F_{S\theta}(t)$ in (5) and (6) are the Langevin noise sources to indicate generation of the induced instantaneous fluctuations on photon number and phase due to spontaneous emission and the process of recombination. These are well approximated as Gaussian distributions with zero mean values and are given by [16]

$$F_{Sp}(t) = \sqrt{\frac{V_{S_p S_p}}{\Delta t}} g_s \quad (16)$$

$$F_{\theta_p}(t) = \sqrt{\frac{V_{S_p S_p}}{\Delta t}} \cdot \frac{g_\theta}{2(S_p + 1)} \quad (17)$$

$$V_{S_p S_p} = \left[\frac{a\xi}{V} (N + N_g) + G_{tho} \right] S_p + \frac{a\xi N}{V} \quad (18)$$

We omit a noise term on the electron extinction in this model because it has a negligible effect on the dynamics in calculated results than those for the photon generation [16]. The electron number $N(t)$ suffers sufficient fluctuation from the Langevin noise sources $F_{Sp}(t)$ through (5), (7) and (12).

In (16) and (17) g_s and g_θ are random number generations in ranges of [14], [16]

$$-1 \leq g_s \leq 1 \quad \text{and} \quad -1 \leq g_\theta \leq 1$$

and Δt is the time-step of the calculation.

The central mode, $p=0$ with wavelength λ_0 , is assumed to lie at the centre of the spectrum of gain. The wavelength of the other modes can be written as

$$\lambda_p = \lambda_0 + p\Delta\lambda = \lambda_0 + p \frac{\lambda_0^2}{2n_r L} \quad p = 0, \pm 1, \pm 2, \pm 3, \dots \quad (19)$$

where $\lambda_0^2/(2n_r L)$ is the longitudinal-mode spacing of solitary laser.

In this paper, effect of the OFB is counted as variation of the equivalent threshold level given by $(c/n_r L) \ln|U_p|$ in (5) and difference of the optical phases between the feedback light and the emitting light $\theta_p(t-\tau) - \theta_p(t)$ in (6), (10) and (11). Counting manner of the phase difference $\theta_p(t-\tau) - \theta_p(t)$ is an alternative method for counting the external modes built between the laser facet and the reflecting point with distance l [2], [10]. In case of numerical simulation, counting of the phase difference is more direct analysis than that of the external modes. Therefore, we do not use the idea of the external modes in this paper. The word ‘mode’ in this paper indicates the longitudinal mode in the solitary laser.

The effect of high-frequency injection is included by modulating the injection current periodically with a modulation frequency f_M . The pumping term I in equation (7) then has to be replaced by

$$I = I_D + I_M \cos(2\pi f_M t) \quad (20)$$

where I_D is the bias current, I_M is the modulation current and f_M is the frequency of sinusoidal modulation.

The rate equations (5)-(7) can be used to obtain the RIN of the diode laser for the modulated signal in the presence of optical feedback by integrating them numerically and calculating the spectrum of intensity fluctuations.

It is to mention that in experiment, the individual modes are not distinguished. Rather, the system performance is governed by the total photon number [3]. The RIN for the total photon number is therefore given by

$$RIN = \frac{\langle S_\Omega^2 \rangle}{|\bar{S}|^2} \quad (21)$$

where S_Ω is calculated from the fluctuations $\delta S(t) = S(t) - \bar{S}$ of the total photon number $S(t) = \sum S_p(t)$ and \bar{S} is the time average of the total photon number.

The values of intensity fluctuation for modulated signal is then computed in terms of RIN by employing the fast Fourier transform to integrate the discrete version of equation (21) as

$$RIN = \frac{1}{|\bar{S}|^2} \frac{\Delta t^2}{T} |FFT[\delta S(t_i)]|^2 \quad (22)$$

We now describe the corresponding numerical procedure that has been followed before we discuss our results in sections IV-VII in detail.

III. PROCEDURE OF NUMERICAL CALCULATION

Parameters used in the numerical calculation are listed in Table I. We include thirteen longitudinal modes in our numerical simulations, which are performed using fourth-order Runge-Kutta algorithm to solve the rate equations (5)-(7) [18]. Time-step of integration is set as short as $\Delta t = 5$ ps. This short time step corresponds to a cutoff Fourier frequency of 100GHz that is high enough to guarantee fine resolution of the OFB

induced dynamics. The length of the external cavity was set to $l = 12$ cm. For the coupling constant we have used $\eta = 0.02$ to estimate the optical feedback ratio Γ .

The integration is first made without OFB for solitary laser from time $t=0$ until the round-trip time $t=\tau$. After $t=\tau$, the OFB is counted by using stored data of $S_p(t-\tau)$ and $\theta_p(t-\tau)$. Dynamics in the steady states are examined after $t=0.5\mu\text{s}$, which is long enough for the transients to be died out. The integration is then proceeded over a long period of time $T=2\mu\text{s}$. This time limit ensures computation of noise as low as 500kHz. RIN is then computed directly from the obtained values of $S(t) = \sum S_p(t)$ by employing the FFT to integrate equation (22).

Note that noise on the calculated RIN spectrum is due to the finite duration of computed time-resolved signal due to our impossibility to simulate infinitely long laser outputs. The RIN spectra are averaged over several trajectories to improve numerical accuracy [19]. The spectra are then smoothed by running an adjacent averaging of spectral components.

Table I. Typical parameter values used in numerical simulations for 850-nm GaAs semiconductor laser

Symbol	Definition	Value	Unit
a	tangential gain coefficient	2.75×10^{-12}	$\text{m}^3 \text{s}^{-1}$
b	dispersion parameter of the linear gain spectrum	3×10^{19}	$\text{m}^3 \text{A}^{-2}$
$ R_{cv} ^2$	squared absolute value of the dipole moment	2.8×10^{-57}	$\text{C}^2 \text{m}^2$
$\delta\lambda$	half-width of spontaneous emission	23	nm
α	linewidth enhancement factor	2.6	-
ζ	confinement factor of field	0.2	-
τ_{in}	electron intraband relaxation time	0.1	ps
τ_S	average electron lifetime	2.79	ns
N_S	electron number characterizing non-linear gain	1.7×10^8	-
N_g	electron number at transparency	2.1×10^8	-
V	volume of the laser active region	100	μm^3
d	thickness of the laser active region	0.11	μm
L	length of the laser active region	300	μm
n_r	refractive index of laser active region	3.6	-
k	internal loss in the laser cavity	10	cm^{-1}
R_f	reflectivity of front facet	0.3	-
R_b	reflectivity of back facet	0.6	-

IV. GENERATION OF OFB NOISE

In this section we outline the main features of intensity noise in semiconductor lasers which will be important for later discussion of noise reduction. Optical feedback affects the noise and dynamics of the laser in different ways, depending on the strength of external feedback. These different effects can be divided into two regimes of feedback as shown in Fig. 2 for a typical 850-nm GaAs laser [2], [12]. The RIN without feedback has a low value (approximately 10^{-16} Hz^{-1}) for frequencies

below 500MHz which corresponds to the quantum noise; and shows a broad peak near 3GHz which corresponds to the relaxation oscillation frequency. The RIN in lower frequency region of the spectrum (<20MHz) appeared to be enhanced by a large amount (>20dB) when the optical feedback ratio Γ was increased from 0 to 2.45×10^{-3} . This RIN enhancement is due to unstable mode hopping between two lasing modes [12]. We call here this type of noise to be low frequency type noise. When OFB ratio was increased more, the RIN profile became flat for wide frequency range from very low frequency to several 100MHz. We call here this type of noise to be flat type noise. This flat-type noise is independent of the mode hopping among lasing modes and is generated due to phase distortion of the lasing modes called the coherence collapse [1], [12].

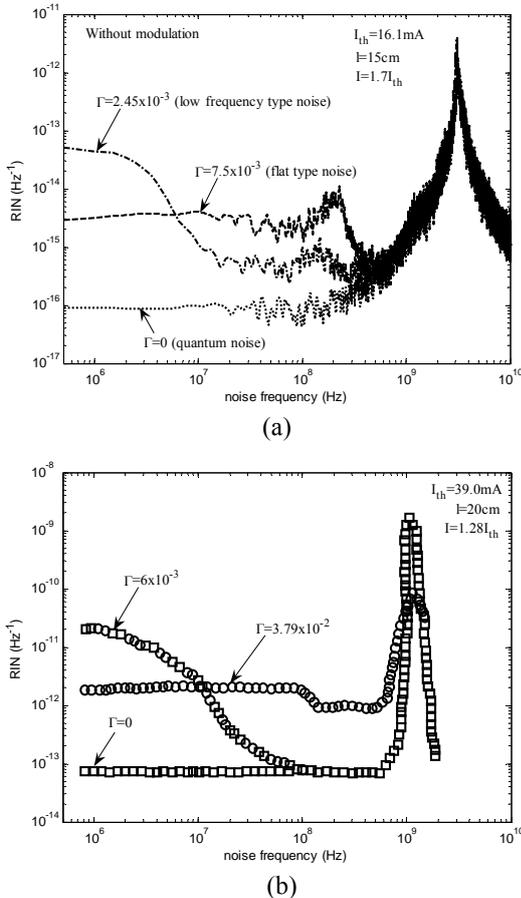


Fig. 2. Spectra of RIN profiles for different OFB strengths; (a) simulated data, (b) experimental results [2]. The OFB noise is classified into the low frequency type and the flat type based on noise frequency profile [12].

Variation of time averaged modal spectrum is shown in Fig. 3 where (a) is for the operation without optical feedback, (b) is the operation under OFB giving increase of the low frequency type noise and (c) is the operation under OFB giving increase of the flat type noise. The laser shows stable single mode when there is no OFB as shown in (a), but changes to multimode operation by the OFB. However, (b) is not pure multimode operation but unstable mode hopping between two modes.

Since the spectrum is time averaged one, it looks like multimode. (c) is in stable multimode operation.

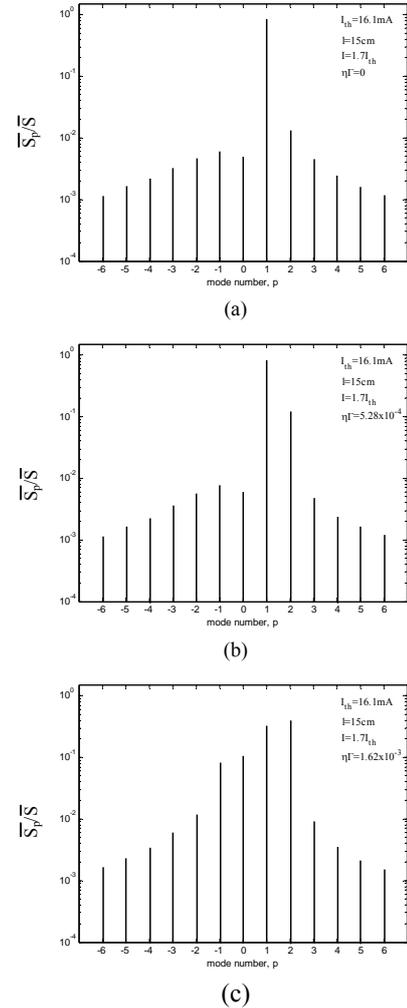


Fig. 3. Time averaged modal spectrum; (a) without OFB, (b) with OFB for low frequency type noise, (c) with OFB for flat type noise. The operation changes to multimode [(b) & (c)] from single mode (a) with OFB.

V. REDUCTION OF OFB NOISE BY SUPERPOSITION OF HF CURRENT

Calculated examples of noise spectrum of the OFB noise and its suppression by superposition of HF current are shown in Fig. 4. The feedback distance is $l=12\text{cm}$ which corresponds to a round trip time period of $f_{ex}=1/\tau=c/2l=1.25\text{GHz}$. Feedback strength is $\Gamma=2.45 \times 10^{-3}$ by which the low frequency type noise is enhanced. Frequency of the superposed HF current is $f_M=500\text{MHz}$. Line spectrum in the figure indicates modulation of the photon number with the HF current and its higher harmonics. Quantum noise spectra are also shown for comparison. The noise is increased more than 20dB by the OFB, and is well suppressed by introduction of the superposition of HF current. Dependency of suppressed noise level with the modulation depth of HF current is shown in Fig. 5. HF

modulation of more than 30% is required to suppress the OFB noise in this numerical example.

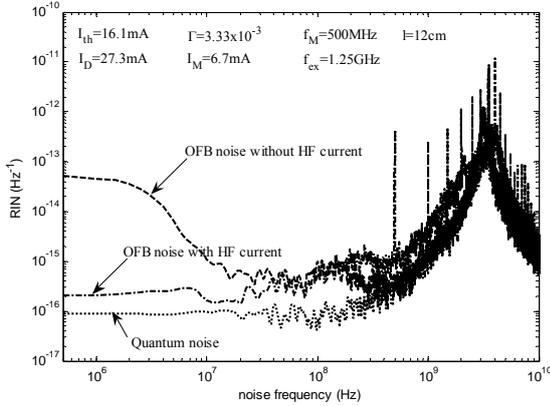


Fig. 4. The simulated spectra of RIN profiles of the OFB noise and suppressed noise by superposition of HF current. The OFB noise is well suppressed by introduction of the HF current.

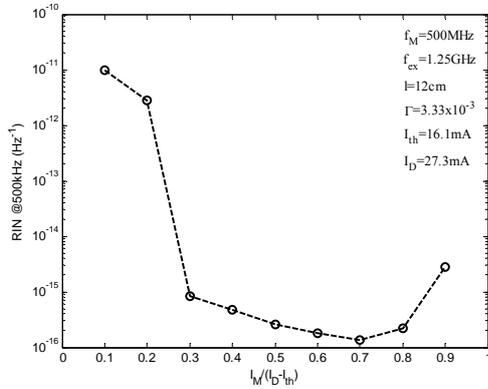


Fig. 5. Dependency of suppressed noise level with the modulation depth of HF current. HF modulation of more than 30% is required to suppress the OFB noise in this numerical example. Frequency of modulation chosen is 500MHz.

Suppression of the OFB noise by the superposition of HF current is not always effective. Dependency of the modulation frequency f_M of the HF current for noise suppression is shown in Fig. 6. The feedback distance is $l=12\text{cm}$ which corresponds $f_{ex}=1.25\text{GHz}$. The RIN is evaluated at the noise frequency of 500KHz. The dashed line indicates the RIN level with neither the OFB nor the superposition of HF current, that is, quantum noise level. The chain line is the RIN level with the OFB but without the HF current. The solid line is the RIN level with the superposition of HF current. The modulation depth is $I_M/(I_D-I_{th})=0.6$ which must be large enough to suppress the OFB noise. The noise is reduced in wide range of the modulation frequency f_M . However, the RIN raises up when modulation frequency f_M of the superposed current coincides with a rational number of the round trip time period f_{ex} .

Fig. 7 shows experimental data of variations of the RIN at 1MHz with the modulation frequency f_M [10]. The feedback distance is $l=21.4\text{cm}$ which corresponds to a round trip time period of $f_{ex}=700\text{MHz}$. The experimental data shows evidence that the OFB noise raises up when f_M and f_{ex} are in rational relations.

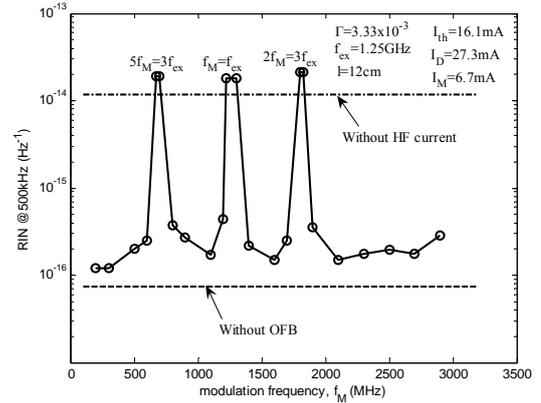


Fig. 6. Calculated data showing dependence of the RIN on modulation frequency of the superposed HF current. The feedback distance is $l=12\text{cm}$ which corresponds to $f_{ex}=1.25\text{GHz}$.

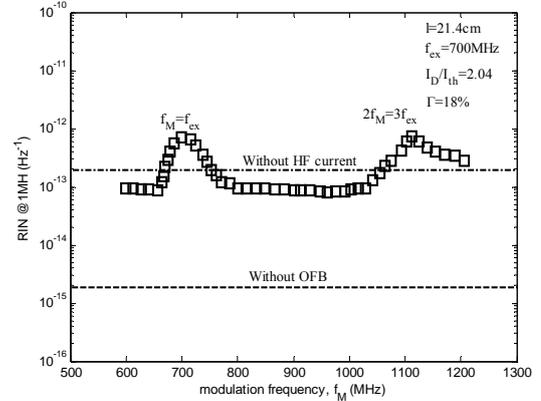


Fig. 7. Experimental data showing dependence of the RIN on modulation frequency of the superposed HF current [10]. The feedback distance is $l=21.4\text{cm}$ which corresponds to $f_{ex}=700\text{MHz}$.

Numerically calculated optical spectrum of the lasing modes are shown in Fig. 8, where (a) is the case that the noise is reduced by the HF current with modulation frequency of 3GHz, that is, $nf_M \neq mf_{ex}$. (b) is the case that the OFB noise raises up with the condition $5f_M=3f_{ex}$. It seems from the spectra of the internal lasing modes of these figures that the laser operates in multimode for both cases – when the noise is reduced and when the noise is increased.

Temporal variations of lasing modes are shown in Fig. 9. Fig. 9(a) is the case that feedback noise is reduced with condition $nf_M \neq mf_{ex}$ corresponding to Fig. 8(a). The lasing modes show stable multimode operation. Fig. 9(b) is the case when the noise raises up with condition $5f_M=3f_{ex}$ corresponding to Fig. 8(b). The lasing modes show unstable mode hopping between $p=+2$ and $p=+1$. From the optical spectrum, by taking time average value, in Fig. 8(b) it looks as if the laser operates in multimode.

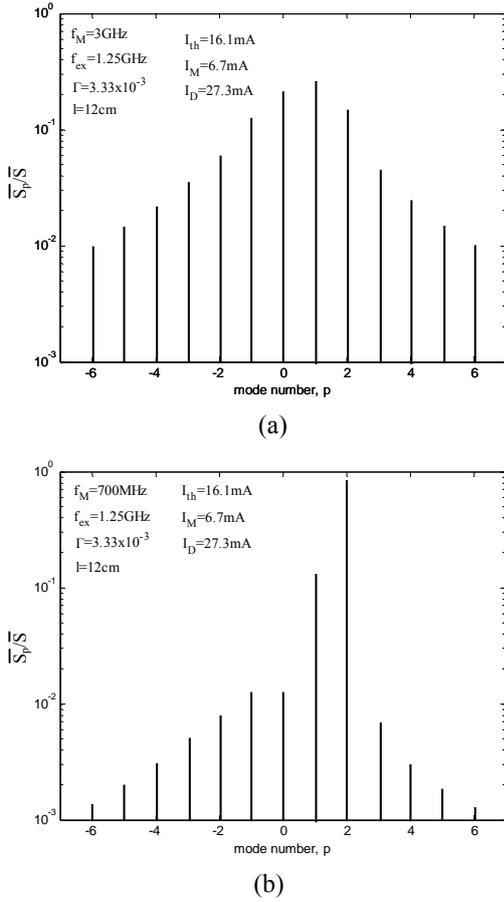


Fig. 8: Longitudinal mode spectrum with the OFB and HF superposition. (a) is the case that feedback noise was reduced with condition $nf_M \neq mf_{ex}$. (b) is the case that the OFB noise raises up with condition $5f_M = 3f_{ex}$.

VI. MECHANISM OF NOISE REDUCTION

Here, we review generating mechanism of the OFB noise and suppression mechanism by the superposition of HF current.

From equations (5) and (8), the variation of the photon number S_p of mode p can be written as,

$$\frac{dS_p}{dt} = (G_p - G_{tho} + C_p)S_p + \frac{\alpha\xi N}{V} + F_{Sp}(t) = \{A_p - B_p S_p - (D_{pq} + H_{pq})S_q - G_{tho} + C_p\}S_p + \frac{\alpha\xi N}{V} + F_{Sp}(t) \quad (23)$$

where

$$C_p = (c/n_r L) \ln|U_p| \quad (24)$$

represents contribution of the OFB to the lasing mode p .

We can obtain a dynamic chart from (23), as shown in Fig. 10, considering two modes p and q . Arrows indicate the flow of the operating point. The lines L_p and L_q indicate conditions $dS_p/dt=0$ and $dS_q/dt=0$, respectively. Operation at steady state is at the point P or Q . If the operation is at P , the laser shows single mode operation with mode p . If the operation is at Q , the laser shows single mode operation with mode q . Selection of the operating point is decided with the initial condition. As

found in this figure, the operating points form bi-stable state in a solitary semiconductor laser.

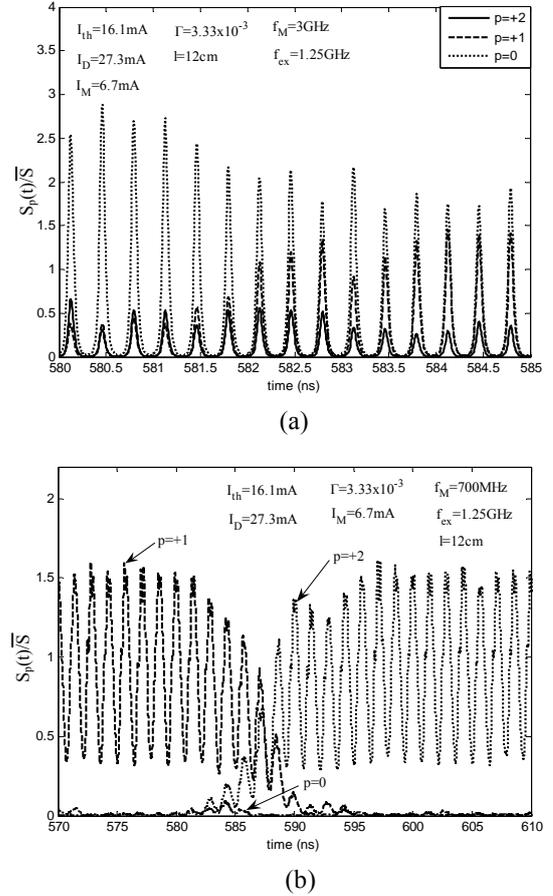


Fig. 9: Temporal variations of all lasing modes. (a) is the case that feedback noise is reduced with condition $nf_M \neq mf_{ex}$ corresponding to Fig. 8(a). The lasing modes show stable multimode operation. (b) is the case when the noise raises up with the condition $5f_M = 3f_{ex}$ corresponding to Fig. 8(b). The lasing modes show unstable mode hopping between $p=+2$ and $p=+1$.

The fluctuating terms $F_{Sp}(t)$ and $F_{Sq}(t)$ give small movements around the steady point P and Q . Since fluctuations are involved in the photon numbers S_p and S_q , and the optical phases θ_p and θ_q , the OFB light has also fluctuations. The stronger the OFB, fluctuations in C_p and C_q become larger through the terms U_p and U_q defined in (10). Then positions of the lines L_p and L_q move randomly, resulting in mode hopping between two operating points P and Q . Since summed value of the photon number $S_p + S_q$ is not constant during the mode hopping the laser reveals large variation on the output power.

Now, if we assume the superposition of HF current, that is, the injection current I is modulated with amplitude I_M and angular frequency $\Omega = 2\pi f_M$,

$$I = \tilde{I} + (I_M e^{j\Omega t} + I_M^* e^{-j\Omega t}) / 2 \quad (25)$$

Corresponding to introduction of the modulation, variations of the electron number N and the photon number S_p are expressed as,

$$N = \tilde{N} + N_M e^{j\Omega t} + N_M^* e^{-j\Omega t} \quad (26)$$

$$S_p = \tilde{S}_p + S_{Mp} e^{j\Omega t} + S_{Mp}^* e^{-j\Omega t} \quad (27)$$

where, \tilde{N} and \tilde{S}_p are slowly varying terms compared with Ω , and N_M and S_{Mp} are modulated terms. By substituting eqn. (26) and (27) into (23), the variation in \tilde{S}_p is given by,

$$\frac{d\tilde{S}_p}{dt} = \left\{ \tilde{A}_p - B_p \tilde{S}_p - (D_{pq} + H_{pq}) \tilde{S}_q - G_{tho} + C_p \right\} \tilde{S}_p + K_p + F_{Sp}(t) \quad (28)$$

with

$$K_p = \frac{a\tilde{\xi}}{V} \left\{ \tilde{N} + N_M S_{Mp}^* + N_M^* S_{Mp} \right\} \quad (29)$$

Similar equations can be obtained for S_q .

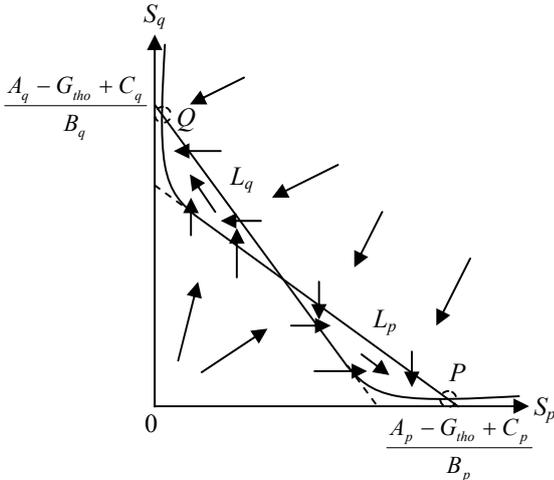


Fig. 10. Dynamic chart indicating mode competition phenomena between two lasing modes. When the OFB level increases the operating point jumps from P to Q or from Q to P .

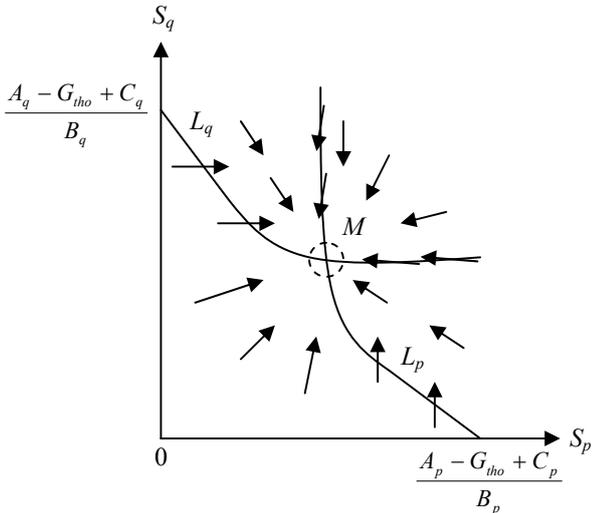
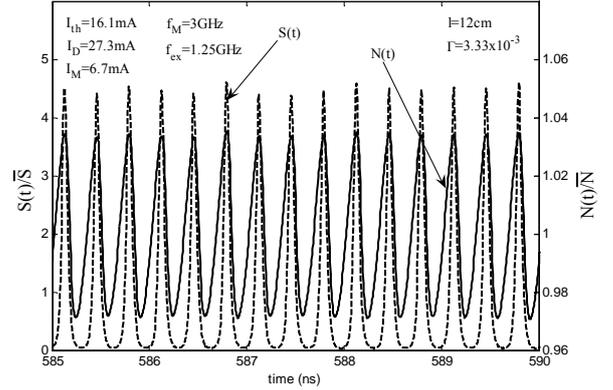


Fig. 11. Change to monostable state by inclusion of HF components in the lasing operation. The operating point M indicates a stable multimode operation of modes p and q .

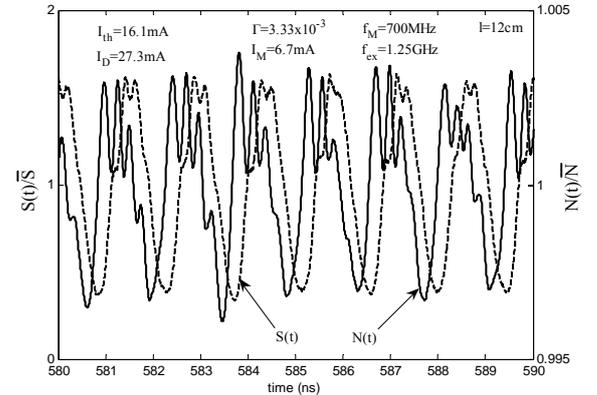
As found from (29), the term K_p is increased by the HF modulation when variation of the electron number N_M and that of the photon number S_M are large enough and in same phase.

With the increase of the term K_p , the lines L_p and L_q concave more strongly achieving a monostable state operation as shown in Fig. 11. The point M is an operating point at steady state, which indicates multimode operation of modes p and q . In this case of Fig. 11, the operating point slightly moves by the OFB, but never shows the mode hopping. The OFB noise is thus suppressed by the superposition of HF current [7], [10].

VII. INVESTIGATION OF THE CONDITIONS UNABLE TO SUPPRESS NOISE



(a)



(b)

Fig. 12. Temporal variations of electron number and total photon number. (a) is the case of $n f_M \neq m f_{ex}$. Variations of the electron number and the photon number are large enough and are in the same phase. (b) is the case of $5 f_M = 3 f_{ex}$. Variation of the electron number and that of the photon number have 90° phase difference. Amplitudes of the variations are small.

As discussed in the previous section, condition to suppress the OFB noise is that, variations of the electron number and the photon number become in the same phase. Calculated values for the temporal variations of the electron number and the total photon number are shown in Fig. 12. (a) is the case of $n f_M \neq m f_{ex}$ with which the OFB noise is well suppressed revealing the stable multimode operation. Variations of the electron number and the photon number are large enough and the varying phases between them are same. (b) is the case of $5 f_M = 3 f_{ex}$ with which the OFB noise is increased with mode hopping remained.

Variation of the electron number and that of the photon number have 90° phase difference. Also, amplitudes of the variations are small. Then the term K_p in (29) cannot increase in this case.

Temporal variations of the gain G_p and the contribution of the OFB $C_p = (c/n_r L) \ln|U_p|$ are shown in Fig. 13. (a) is the case of $mf_M \neq nf_{ex}$ with which the OFB noise is well suppressed. (b) is the case of $5f_M = 3f_{ex}$ with which the OFB noise is increased with mode hopping remained. We find that the variations of G_p and C_p are not synchronized when $mf_M \neq nf_{ex}$, as shown in (a), but are synchronized with f_M having almost 180° phase difference when $5f_M = 3f_{ex}$ as shown in (b). In the case of $mf_M \neq nf_{ex}$, the phase difference between the feedbacked light and emitting light, $\theta_p(t-\tau) - \theta_p(t)$ in (10), has no fixed relation. Then, variations of the electron number N and the gain coefficient G_p are not disturbed by the OFB, resulting in sufficient variation of the photon number S_p . However, in the case of $mf_M = nf_{ex}$, the phase difference $\theta_p(t-\tau) - \theta_p(t)$ is locked with the rational frequency of f_M [20] and works to reduce variation of $G_p + C_p$ for variations of G_p and C_p are in inverse phase relation as shown in Fig. 13(b). Then the modulation of the photon number is reduced as found from (5) or (23).

VIII. CONCLUSION

Semiconductor lasers tend to be suffered by the optical feedback (OFB) noise caused by reflection of the output light at surface of the optical disc or the optical fiber. Superposition of high frequency (HF) current is the most popularly used technique to suppress the OFB noise. However, noise suppression by the superposition of HF current does not work when the modulation frequency of the HF current coincides with a rational number of the round trip time for the OFB.

A simulation model giving generation of the OFB noise and its suppression by the superposition of HF current is shown in this paper. Mode competition phenomena among lasing modes in the solitary laser and optical phase delay between the feedbacked light and emitting light were counted in the model together with the Langevin noise sources to explain generation of the OFB noise. The highest OFB noise is caused by the mode competition phenomena among lasing modes which is induced by the OFB.

The superposition of HF current works to modulate both the electron number N and the photon number S_p , which works to change the operating state from the bi-stable state to the monostable state, and stop the mode hopping resulting in suppression of the OFB noise. However, when the modulation frequency f_M of the superposed HF current coincides with a rational number of the returning period f_{ex} of the OFB, modulations of the electron number N and the photon number S_p are suppressed by the phase locking effect with undesirable phase relation, resulting in reduced modulation of N and S_p . Thus the noise suppression effect does not work under the condition $nf_M = mf_{ex}$.

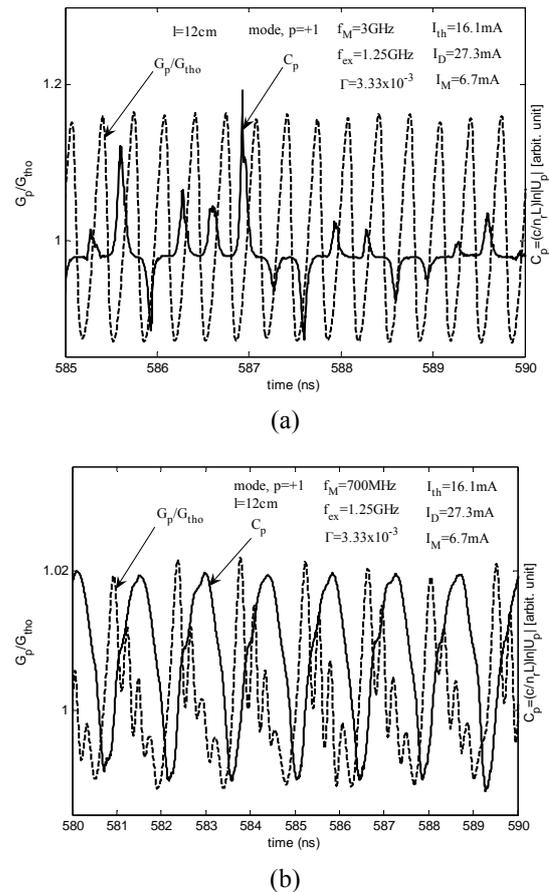


Fig. 13. Temporal variations of the gain G_p and the contribution of the OFB C_p . (a) is the case of $mf_M \neq nf_{ex}$ with which the OFB noise is well suppressed. (b) is the case of $5f_M = 3f_{ex}$ with which the OFB noise is increased with the mode hopping remained. Variations of G_p and C_p are not synchronized when $mf_M \neq nf_{ex}$ as in (a), but are synchronized with f_M and have almost 180° phase difference when $5f_M = 3f_{ex}$ as in (b).

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